

L Number	Hits	Search Text	DB	Time stamp
1	1	"6710391"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:58
2	1	"20040000686"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:59
4	202	houston-theodore-w.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:59
5	21	houston-theodore-w.in. and DRAM and capacitor and ground	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:59
6	19	(houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:59
7	5	((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:59
8	5	((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 10:59
9	2	((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "6255603") and DRAM and ground	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:00
3	8	("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "6255603")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:08
10	660	DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:09
11	406	(DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:11
12	400	((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:35
13	386	DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:17
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((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "6255603") and DRAM and ground) and ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5)				
((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "6255603") and DRAM and ground) and ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5)				

23	0	20040012022.URPN.	USPAT	2004/07/09 11:21
24	1	"6562679".PN.	USPAT	2004/07/09 11:25
25	0	6727542.URPN.	USPAT	2004/07/09 11:25
26	9	("4864374" "5229326" "5998225" "6236079" "6297525" "6329684" "6352896" "6436762" "6555891").PN.	USPAT	2004/07/09 11:26
27	0	6746915.URPN.	USPAT	2004/07/09 11:27
28	0	6746915.URPN.	USPAT	2004/07/09 11:27
29	55	((((((((((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 and (contact)) not (((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 and (contact adj pillar))) and (method or process)) and (method or process)) and (second adj (dielectric or insulati\$4))) and ((second adj (dielectric or insulati\$4)) with (etch\$4 or remov\$4))) and (capacitor with (plate or electrode))) and expos\$4) and (expos\$4 with (etch\$4 or remov\$4))) not memory and (capacitor and ground and adj pillar and ground and plate and insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. "20040000686" theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:31
30	3	memory and (capacitor and ground and adj pillar and ground and plate and insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. "20040000686" theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/07/09 11:34
31	10	memory and (capacitor and ground and adj pillar and ground and plate and insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. "20040000686" theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5)	USPAT	2004/07/09 11:33
32	0	memory and (capacitor and ground and adj pillar and ground and plate and insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. "20040000686" theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5)	USPAT	2004/07/09 11:34

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 capacitor and ground) and (method or
 process)) and planariz\$5)

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